

N- Channel 70-V (D-S) MOSFET

1. Description

The HP1010E is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

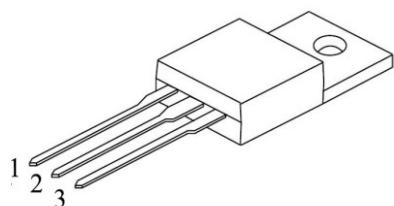
2. Feature

- $R_{DS(on)Typ} \leq 6m\Omega @ V_{GS}=10V$
- Low ON Resistance
- Low Gate Charge
- Peak Current vs Pulse Width Curve

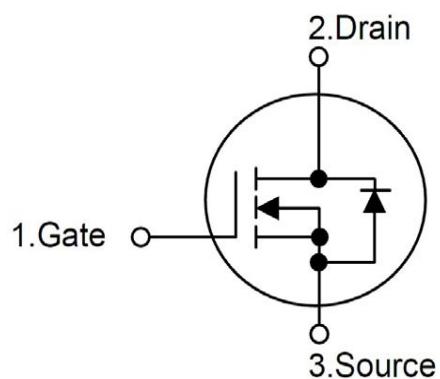
V _{DS}	70	V
R _{DS(on)Typ}	6	mΩ
I _D	90	A

3. Pin configuration

Order Number	Package
HP1010E	TO-220



TO-220



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4. Absolute maximum ratings (Tc=25°C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DSS}	70	V
Gate-Source Voltage		V _{GSS}	±25	V
Continuous Drain Current	T _c =25°C	I _D	90	A
	T _c =100°C		65	A
Pulsed Drain Current		I _{DM}	320	A
Power Dissipation	T _c =25°C	P _D	130	W
	Derating Factor above 25°C		1.54	W/°C
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

5. Thermal characteristics

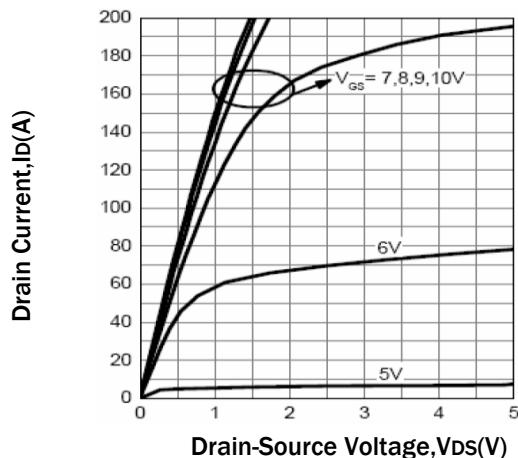
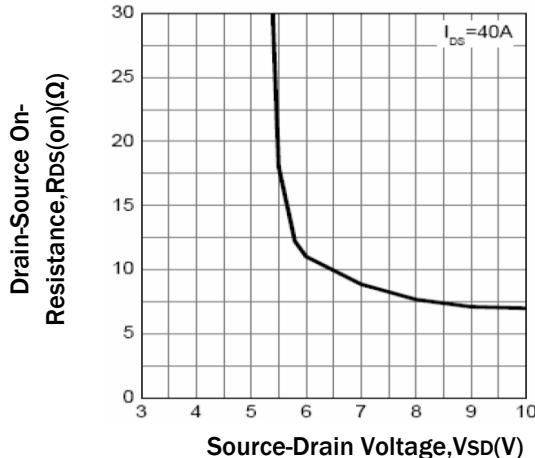
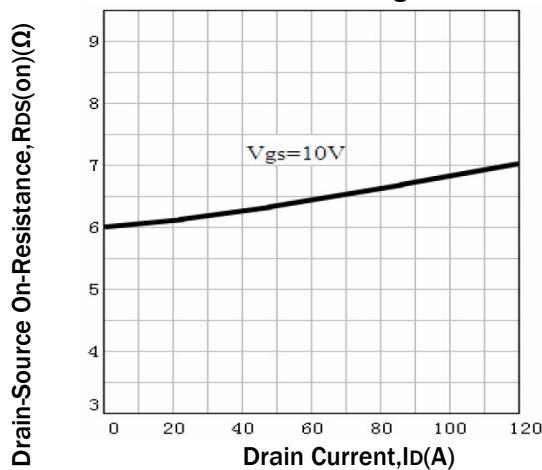
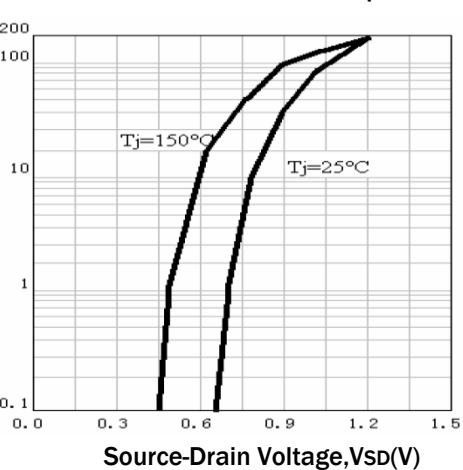
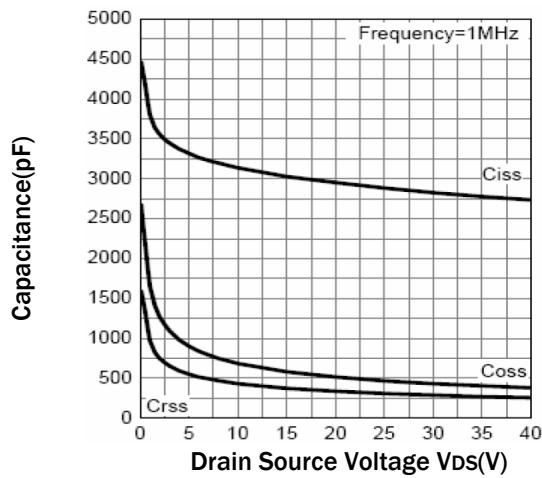
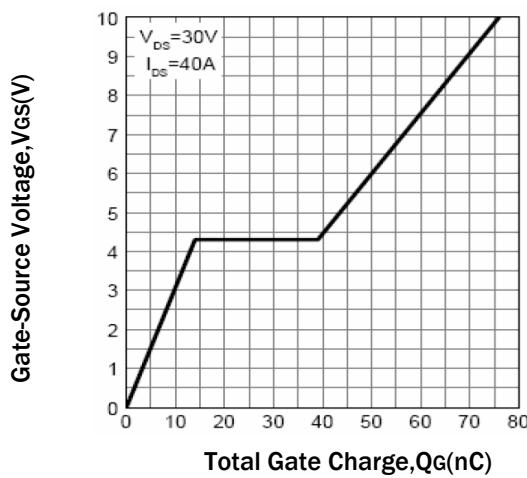
Parameter	Symbol	Ratings	Units
Thermal resistance, case-to-sink typ.	R _{thCS}	0.5	°C/W
Thermal resistance junction to case.	R _{thJC}	0.65	°C/W
Thermal resistance junction to ambient.	R _{thJA}	62	°C/W

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6. Electrical characteristics ($T_A = 25^\circ C$ Unless Otherwise Specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
STATIC						
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	70	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2	-	4	V
I _{GSS}	Gate-Body Leakage	V _{DS} =0V, V _{GS} =±25V	-	-	±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =68V, V _{GS} =0V	-	-	1	μA
R _{D(S(ON))}	Drain-Source On-Resistance	V _{GS} =10V, I _D =35A	-	6	8	mΩ
V _{SD}	Diode Forward Voltage	I _S =20A, V _{GS} =0V	-	-	1.5	V
DYNAMIC						
Q _g	Total Gate Charge	V _{DD} =30V, V _{GS} =10V, I _D =30A	-	65	-	ns
Q _{gs}	Gate-Source Charge		-	12	-	
Q _{gd}	Gate-Drain Charge		-	21	-	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	2900	-	pF
C _{oss}	Output Capacitance		-	340	-	
C _{rss}	Reverse Transfer Capacitance		-	200	-	
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, I _D =1A, V _{DD} =30V, R _G =8Ω	-	13	-	ns
t _r	Turn-On Rise Time		-	15	-	
t _{d(off)}	Turn-Off Delay Time		-	29	-	
t _f	Turn-Off Fall Time		-	55	-	
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _F =40A, di/dt=100A/us	-	49	-	ns
Q _{rr}	Reverse Recovery Charge		-	93	-	

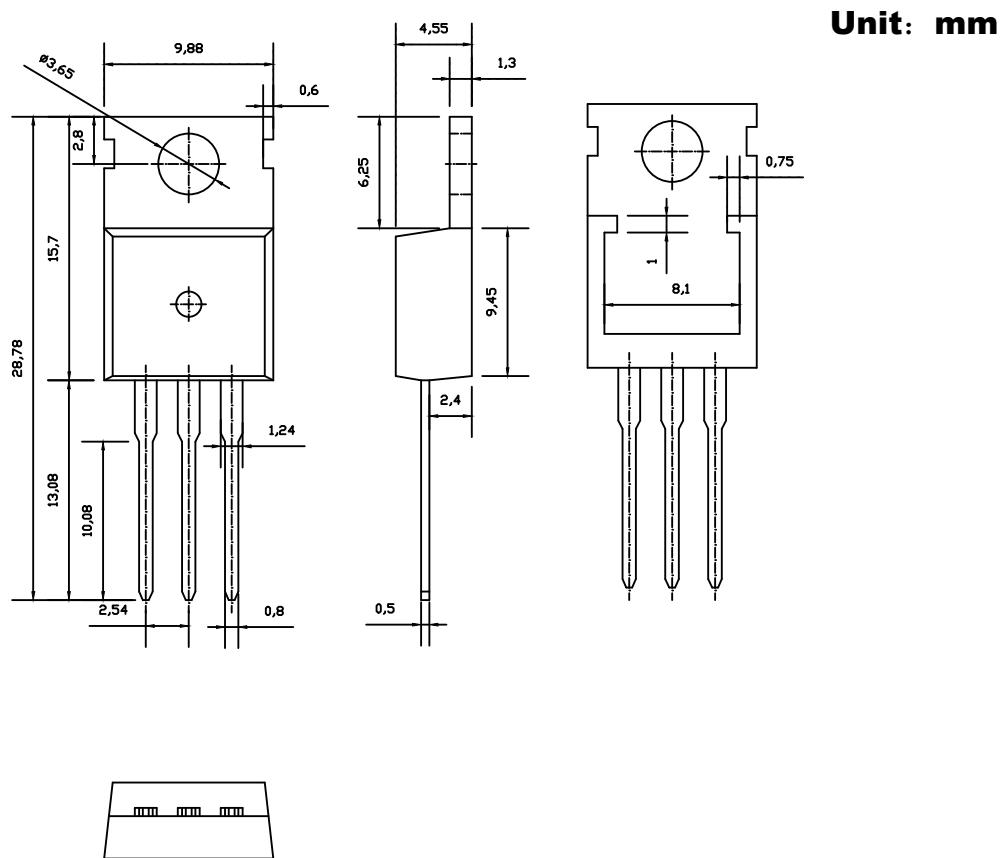
Notes :a. pulse test:pulse width 300 us,duty cycle 2% ,Guaranteed by design,not subject to production testing.

YOMOS reserves the right to improve product design,functions and reliability without notice.

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7. Typical Characteristics ($T_J = 25^\circ\text{C}$ Noted)
On-Region Characteristics

Drain-Source On Resistance

On-Resistance Variation vs. Drain Current and Gate Voltage

Body Diode Forward Voltage Variation vs. Source Current and Temperature

Capacitance Characteristics

Gate Charge vs. Gate-to-Source Voltage


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8.Package Information:



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